

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A light emitting device comprising
a semiconductor light emitting component; and
a phosphor capable of absorbing a part of light emitted by the light emitting component and emitting light of wavelength different from that of the absorbed light,
wherein a straight line connecting a point of chromaticity corresponding to a peak of the spectrum generated by the light emitting component and a point of chromaticity corresponding to a peak of the spectrum generated by the phosphor is along with the black body radiation locus in the chromaticity diagram.
2. (Original) The light emitting device according to claim 1,
wherein said light emitting component is a blue LED.
3. (Currently Amended) The light emitting device according to claim 1,
wherein said point of chromaticity corresponding to a peak of the spectrum generated by the light emitting component, said point of chromaticity corresponding to a peak of the spectrum generated by the phosphor and contents of the phosphor are adjusted so that said straight line is along with the black body radiation locus.

4. (Currently Amended) The light emitting device according to claim 1,
wherein said straight line contains a point corresponding to a color temperature of about 8080K or 4400K.
5. (Currently Amended) The Light light emitting device according to claim 1,
wherein a main emission peak of the light emitting component is set within the range from about 400nm to 530 nm.
6. (Currently Amended) The light emitting device according to claim 1,
wherein a main emission peak of the light emitting component is set within the range from about 420 nm to 490 nm.
7. (Currently Amended) The light emitting device according to claim 1,
wherein a main emission peak of the light emitting component is set within the range from about 450 nm to 475 nm.
8. (Original) The light emitting device according to claim 1,
wherein the structure of the light emitting component is either one structure of homostructure, heterostructure and double-heterostructure which have MIS junction, PIN junction or PN junction.

9. (Original) The light emitting device according to claim 1,

wherein said light emitting component comprises an active layer having a single quantum well structure or multi quantum well structure.

10. (Original) The light emitting device according to claim 1,

wherein said phosphor is made by steps of solving rare earth elements in acid in stoichiometrical proportions, coprecipitating the solution with oxalic acid to obtain a sediment, firing the sediment to obtain an oxide, and firing a mixture of said oxide, an ammonium fluoride and aluminum oxide.

11. (Currently Amended) The light emitting device according to claim 1,

wherein an emission peak of the phosphor is set within the range from about 530 nm to 570 nm.